

Improving the charge collection efficiency in GridPix

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GridPix Model — Amplification gap and drift region

Geometry

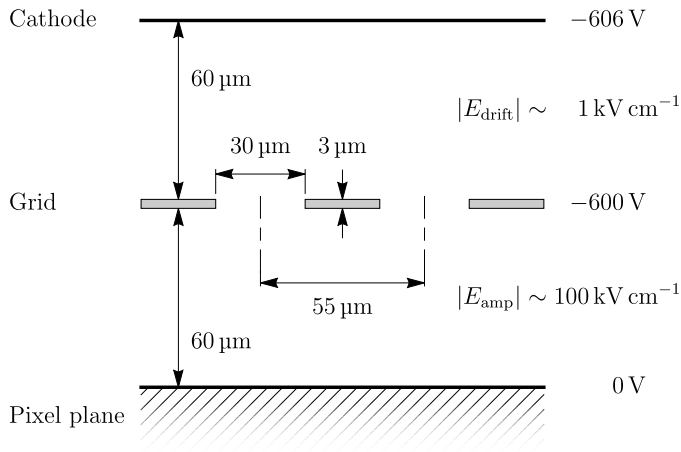
- Hole diameter: $30\ \mu\text{m}$
- Amplification gap: $60\ \mu\text{m}$

Fields

- Drift: $1\ \text{kV cm}^{-1}$
- Amplification: $100\ \text{kV cm}^{-1}$

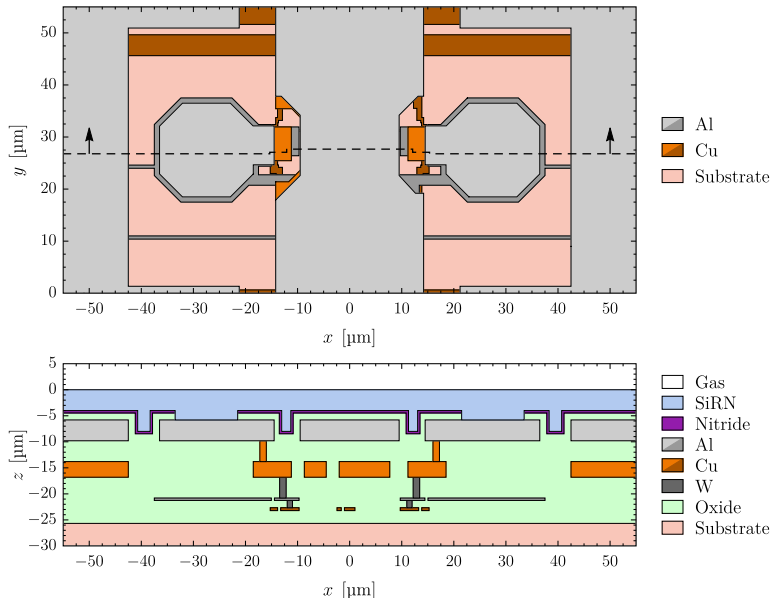
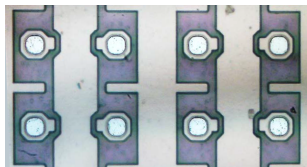
Gas

- DME(50 %)/CO₂(50 %)



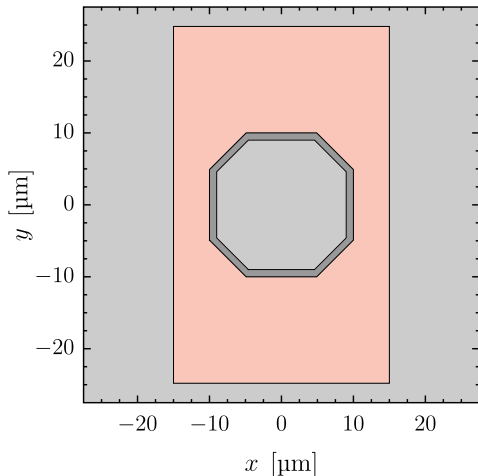
GridPix Model — TPX3 pixel chip

- Need pixel plane model for signal calculation
- First find out what TPX3 really looks like
- Pad diameter is $18\ \mu\text{m}$
- Passivation opening diameter is $12\ \mu\text{m}$

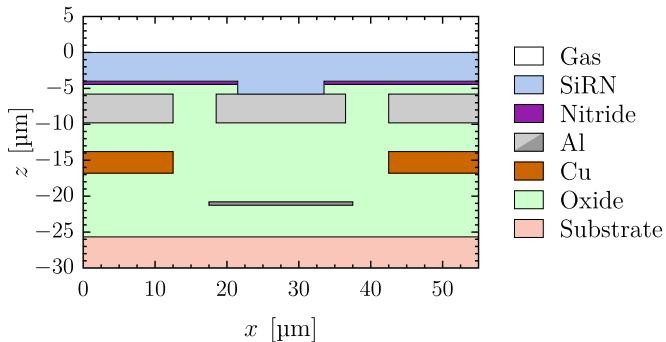


GridPix Model — TPX3 pixel chip

Top view

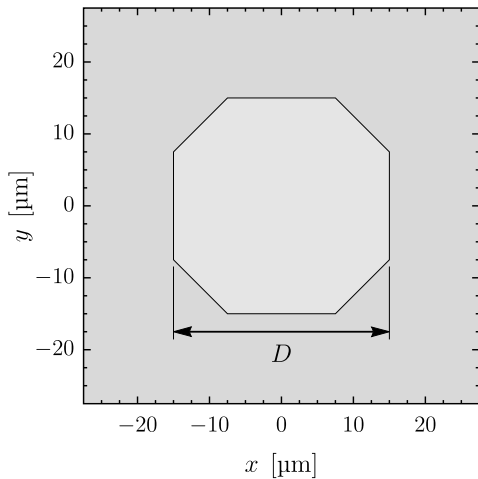


Cross section

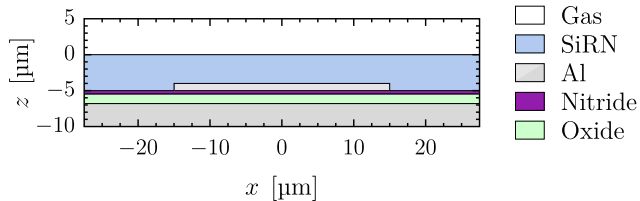


GridPix Model — Pixel pad enlargement

Top view



Cross section



Charge Collection — Shockley-Ramo theorem

- Instantaneous current on pad:

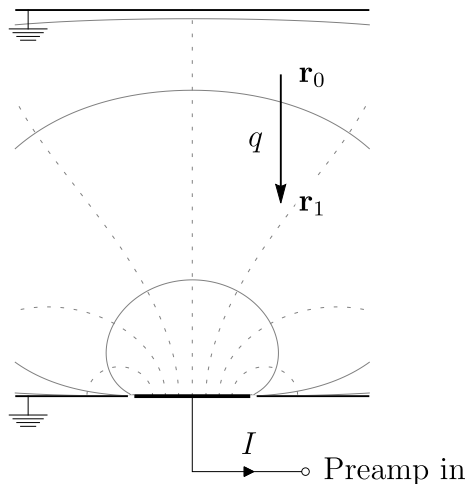
$$I = -q \boldsymbol{\psi} \cdot \frac{d\mathbf{r}}{dt}$$

with $\boldsymbol{\psi} = \frac{\mathbf{E}_w}{1V}$

- Integrated signal of charge q moving from \mathbf{r}_0 to \mathbf{r}_1 :

$$Q = \int_{t_0}^{t_1} dt I = q [\phi(\mathbf{r}_1) - \phi(\mathbf{r}_0)]$$

with ϕ such that $\boldsymbol{\psi} = -\nabla\phi$



Charge Collection — Electron ion pair

- Charge induced by electron:

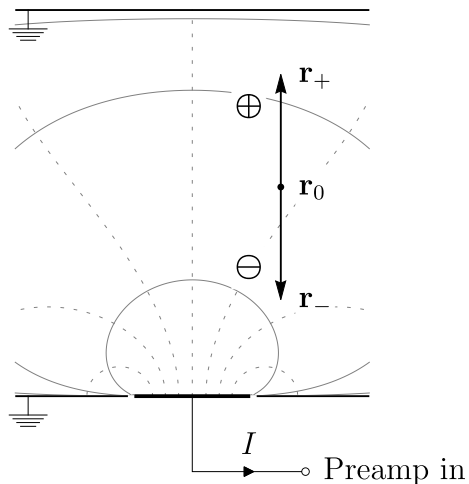
$$Q_- = [\phi_- - \phi_0] e^-$$

- Charge induced by ion:

$$Q_+ = [0\text{ V} - \phi_0] (-e^-) = \phi_0 e^-$$

- Total signal charge:

$$Q = Q_+ + Q_- = \phi_- e^-$$



Charge Collection — Avalanche

- Charge induced by electron:

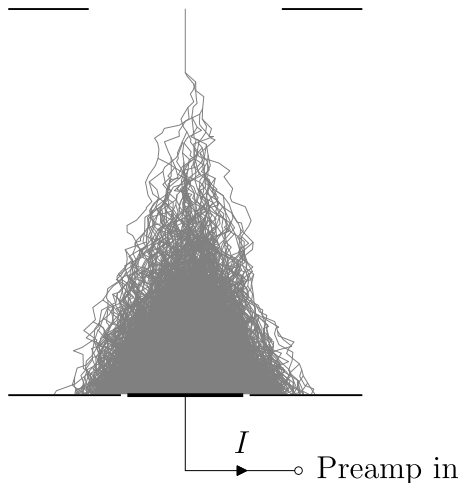
$$Q_- = \sum_{n=1}^N [\phi_{-,n} - \phi_{0,n}] e^- = [\bar{\phi}_- - \bar{\phi}_0] N e^-$$

- Charge induced by ion:

$$Q_+ = \sum_{n=1}^N \phi_{0,n} e^- = \bar{\phi}_0 N e^-$$

- Total signal charge:

$$Q = Q_+ + Q_- = \bar{\phi}_- N e^-$$



Charge Collection — Avalanche

- Electrons move very fast compared to ions

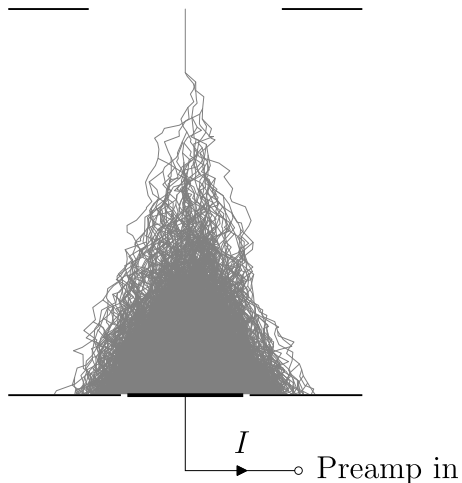
	$v_{\text{drift}} [\mu\text{m ns}^{-1}]$
electrons	230
ions	0.74

- For a 60 μm amplification gap:

$$Q(t = 0) = 0$$

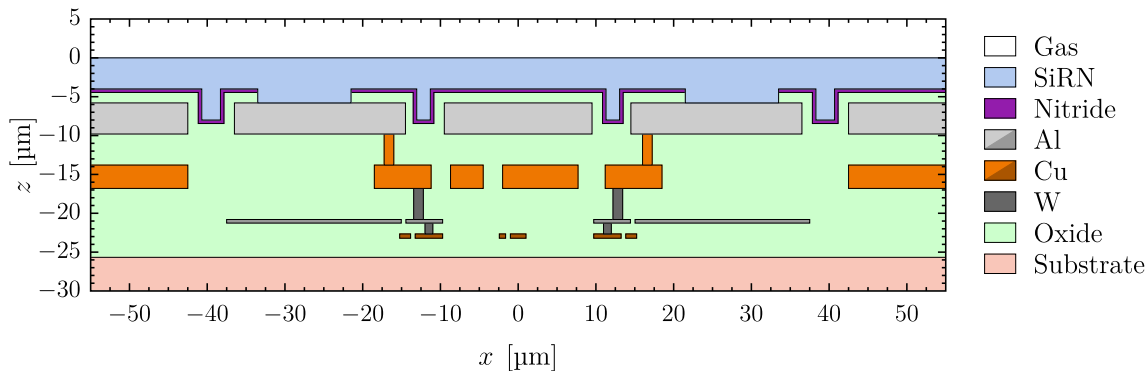
$$Q(t \approx 0.26 \text{ ns}) = Q_-$$

$$Q(t \approx 81 \text{ ns}) = Q_+ + Q_-$$



Charge Collection — Protection layer

- Protection layer is slightly conductive
- How does this affect the signal calculation?



Charge Collection — Protection layer

- After an avalanche:

$$\sigma(t=0) = \frac{Q_{\text{ava}}}{55 \times 55 \mu\text{m}^2}$$

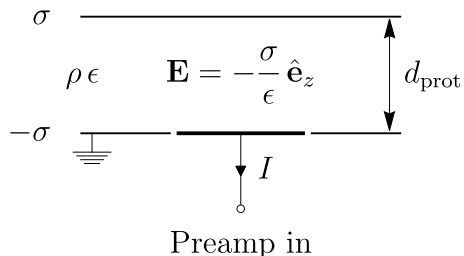
- This sets up a current density inside the protection layer:

$$\mathbf{J} = \frac{\mathbf{E}}{\rho} = -\frac{\sigma}{\rho\epsilon} \hat{\mathbf{e}}_z$$

- The surface charge now changes as

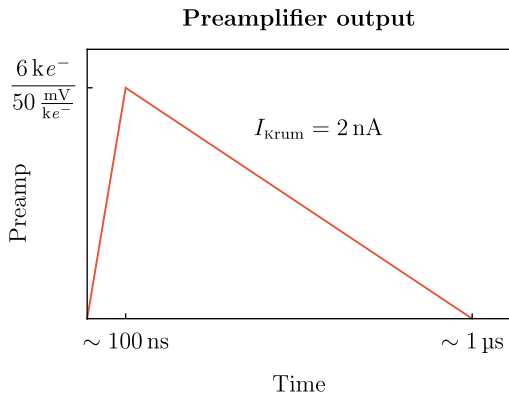
$$\frac{d\sigma}{dt} = \mathbf{J} \cdot \hat{\mathbf{e}}_z = -\frac{\sigma}{\rho\epsilon} \Rightarrow \sigma(t) = \sigma(0) \exp\left(-\frac{t}{\rho\epsilon}\right)$$

- Any change in the signal will be on a time scale of $\rho\epsilon$



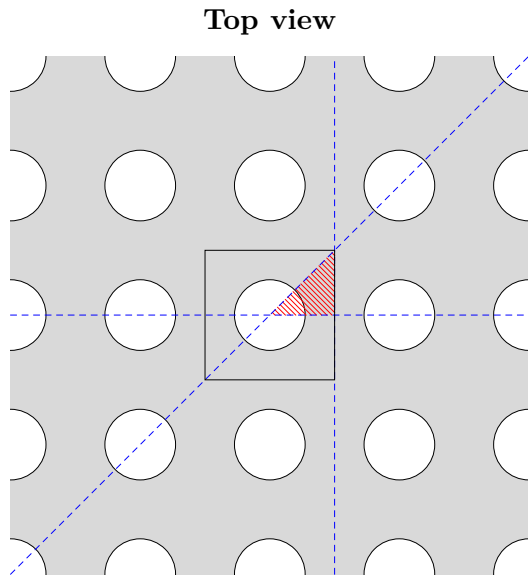
Charge Collection — Protection layer

- Preamplifier output returns to baseline in $\sim 1 \mu\text{s}$
- For SiRN, ρ is somewhere in the range of 10^9 – $10^{13} \Omega\text{m}$. So, $\rho\epsilon$ is somewhere in the range of 60 ms–600 s
- Therefore, we can safely regard the protection layer as an insulator for signal calculations



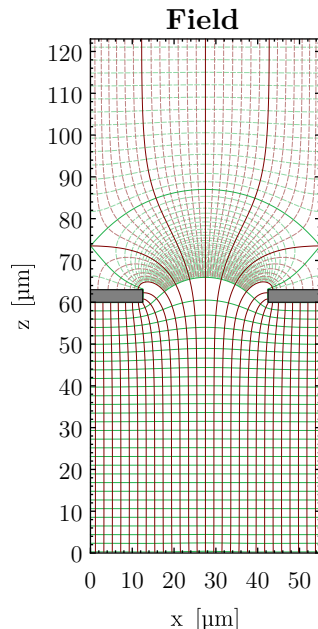
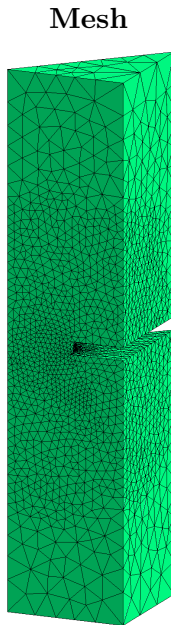
Meshing and electric field calculation

- Use mirror symmetries to reduce number of finite elements in field and detector simulation
- Boundary condition on planes of mirror symmetry: $\nabla V \cdot \hat{n} = 0$
- Only simulate fields in shaded region

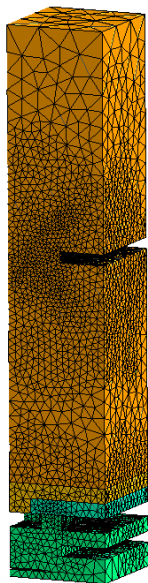


Meshing and electric field calculation

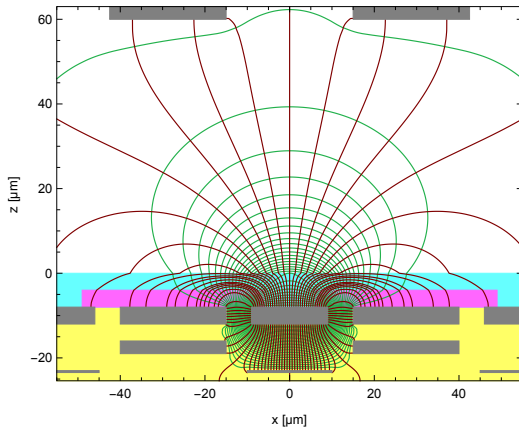
- We mesh the geometry with Gmsh
 - 3D finite element grid generator (free software)
- We use Elmer to calculate the field
 - Open source multiphysical simulation software mainly developed by CSC-IT Center for Science
- To save CPU, the mesh only extends up to $123\ \mu\text{m}$. Above that, the field is constant.



Mesh

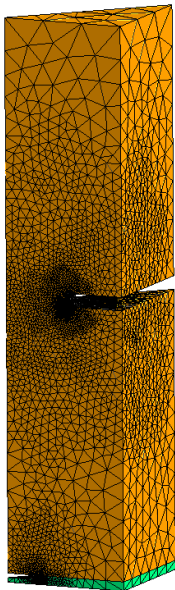


W-field

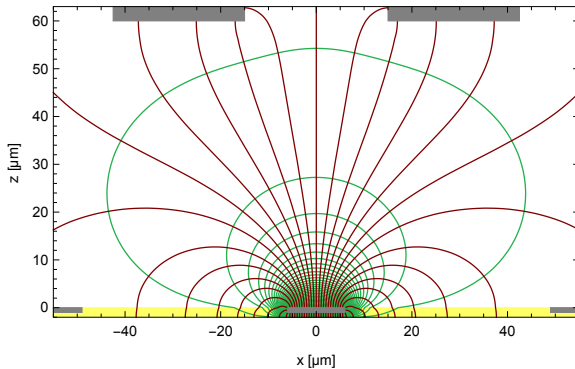


Meshing and electric field calculation — Enlarged pad

Mesh



W-field



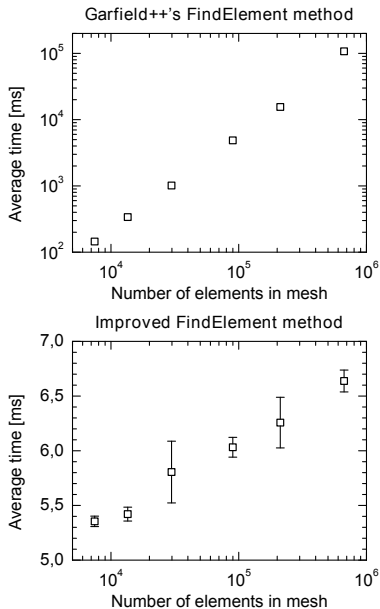
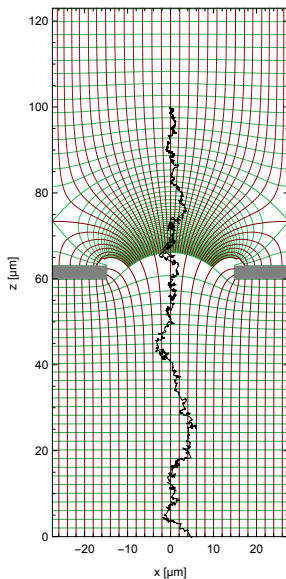
Meshing and electric field calculation — Speeding up Garfield++

- FindElement function was taking up $> 90\%$ of computation time
- Measure average time to find elements along an electron track consisting of 7695 points
- Garfield++'s FindElement: $\mathcal{O}(n)$
- Improved FindElement: $\mathcal{O}(\log n)$

Speedup for my mesh:

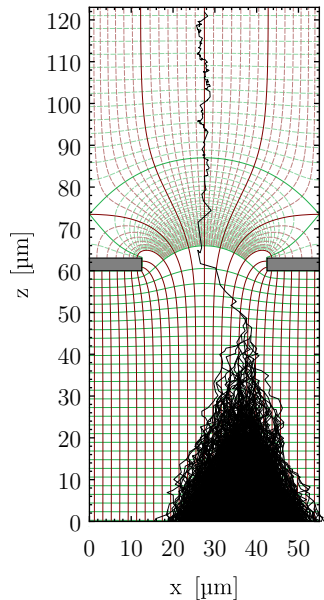
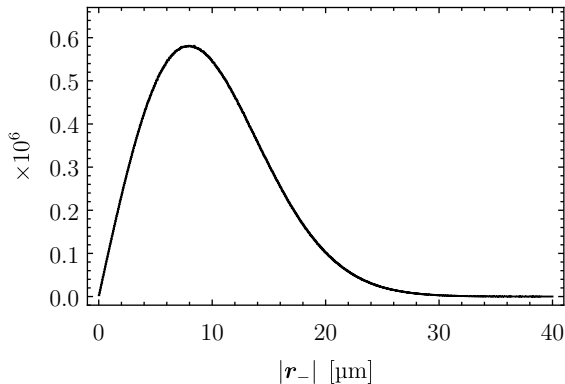
- FindElement: ~ 62 times faster
- Garfield++: ~ 25 times faster

Benchmarking event

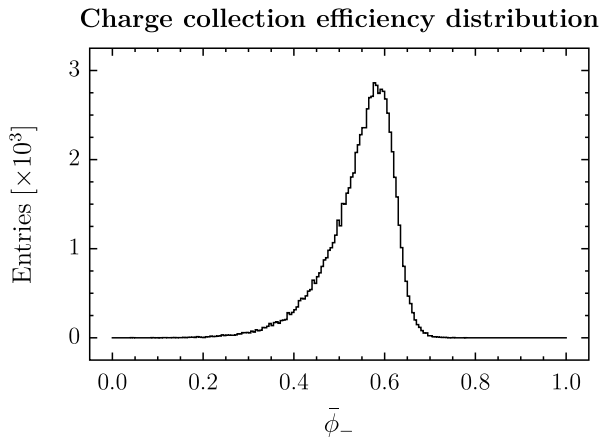


Simulating avalanches with Garfield++

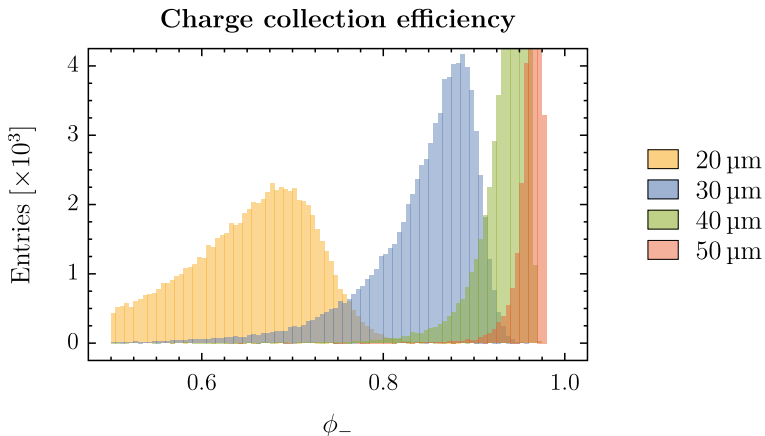
Electron endpoint distribution



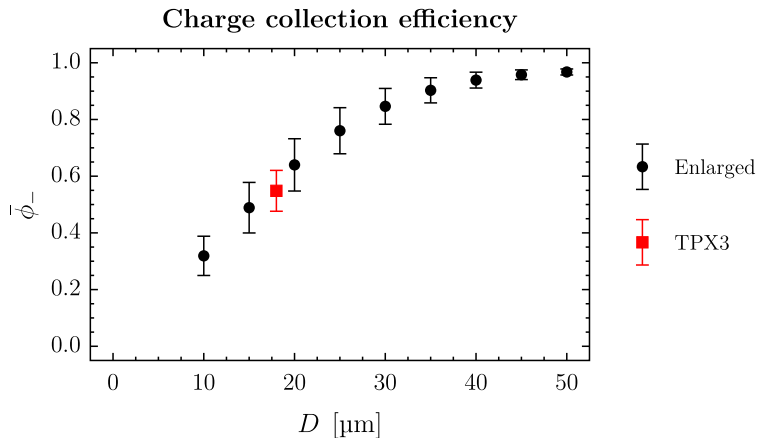
Entries	8.1×10^4
Mean	0.55
RMS	0.07



Charge collection efficiency — Enlarged pixel pad

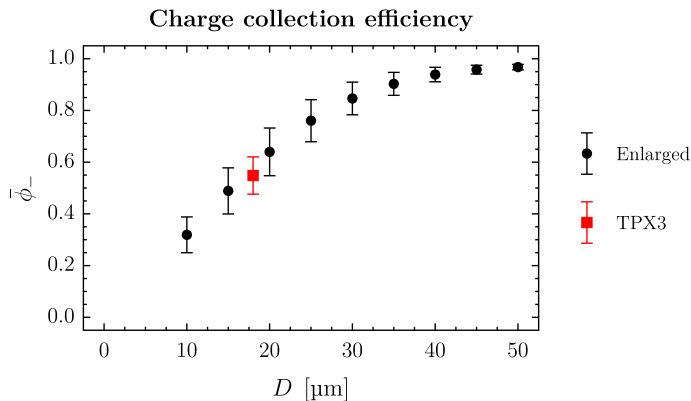


Charge collection efficiency — Enlarged pixel pad



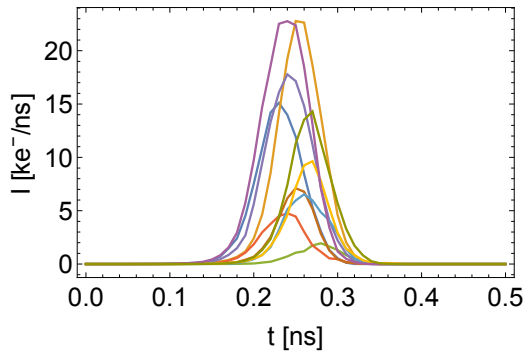
Conclusions:

- Increasing the pixel pad size will increase the charge collection efficiency
- Alternatively, the gas gain can be reduced to increase the durability

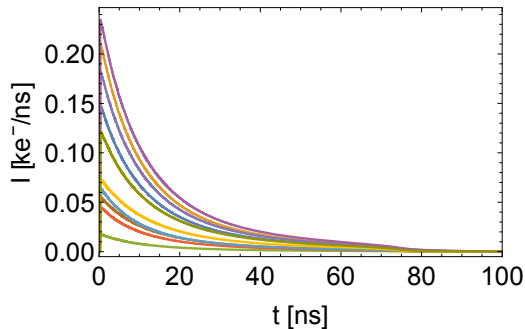


Time dependent signal

Current induced by electrons



Current induced by ions



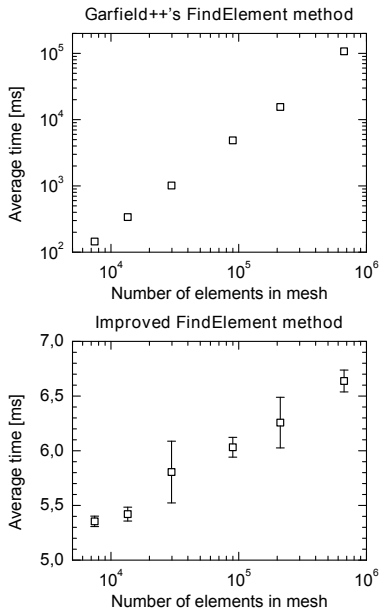
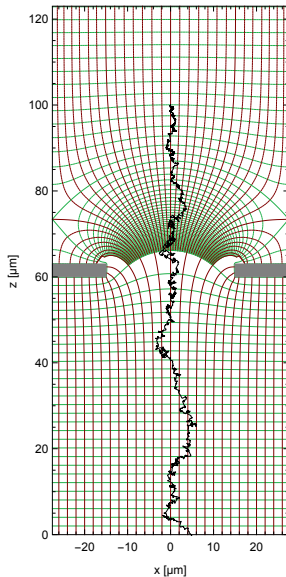
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Speedup for my mesh:

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Benchmarking event



Charge buildup

